

Holger Bartolf

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8986648/publications.pdf>

Version: 2024-02-01

32
papers

483
citations

1162367

8
h-index

713013

21
g-index

32
all docs

32
docs citations

32
times ranked

636
citing authors

#	ARTICLE	IF	CITATIONS
1	Evidence for carbon clusters present near thermal gate oxides affecting the electronic band structure in SiC-MOSFET. Applied Physics Letters, 2019, 115, .	1.5	19
2	Tailoring the 4H-SiC/SiO ₂ MOS-interface for SiC-based power switches. Japanese Journal of Applied Physics, 2016, 55, 08PC04.	0.8	2
3	A novel edge termination for high voltage SiC devices. , 2016, , .		8
4	High Channel Mobility 4H-SiC MOSFETs by As and P Implantation Prior to Thermal Oxidation in N ₂ O Atmosphere. Materials Science Forum, 2016, 858, 651-654.	0.3	3
5	Dopant imaging of power semiconductor device cross sections. Microelectronic Engineering, 2016, 160, 18-21.	1.1	11
6	Fluctuation Mechanisms in Superconductors. , 2016, , .		11
7	Large area scanning probe microscope in ultra-high vacuum demonstrated for electrostatic force measurements on high-voltage devices. Beilstein Journal of Nanotechnology, 2015, 6, 2485-2497.	1.5	6
8	Improving the Design of the Shield for the Electric Field in SiC-Based Schottky-Rectifiers and Ion-Implantation Cascades by SPM Dopant-Imaging. Microelectronic Engineering, 2015, 148, 1-4.	1.1	6
9	JBS power-rectifiers for 1.7kV applications with conduction properties close to pure Schottky-design. , 2015, , .		2
10	Device Simulations on Novel High Channel Mobility 4H-SiC Trench MOSFETs and Their Fabrication Processes. Microelectronic Engineering, 2015, 145, 166-169.	1.1	4
11	Passivation of 4H-SiC/SiO ₂ Interface Traps by Oxidation of a Thin Silicon Nitride Layer. Materials Science Forum, 2015, 821-823, 508-511.	0.3	2
12	Inversion-Channel MOS Devices for Characterization of 4H-SiC/SiO ₂ Interfaces. Materials Science Forum, 2015, 821-823, 480-483.	0.3	3
13	Development of power semiconductors by quantitative nanoscale dopant imaging. , 2015, , .		0
14	Development of a 60 μm Deep Trench and Refill Process for Manufacturing Si-Based High-Voltage Super-Junction Structures. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 529-541.	1.4	23
15	Current-assisted thermally activated flux liberation in ultrathin nanopatterned NbN superconducting meander structures. Physical Review B, 2010, 81, .	1.1	122
16	Nanoscale fabrication by intrinsic suppression of proximity-electron exposures and general considerations for easy and effective top-down fabrication. Journal of Micromechanics and Microengineering, 2010, 20, 125015.	1.5	6
17	Magnetic vortices in superconducting photon detectors. Journal of Modern Optics, 2009, 56, 352-357.	0.6	2
18	Optical and transport properties of ultrathin NbN films and nanostructures. Physical Review B, 2009, 80, .	1.1	148

#	ARTICLE	IF	CITATIONS
19	NbN superconducting nanowire photon counters: magnetoconductivity and other detector properties. , 2009, , .		1
20	Current-Induced Critical State in NbN Thin-Film Structures. Journal of Low Temperature Physics, 2008, 151, 585-590.	0.6	17
21	metallic structures with lateral dimensions less than 15nm and $\langle \text{mml:math} \text{ altimg= 'si6.gif' overflow= 'scroll' xmlns:xocs= 'http://www.elsevier.com/xml/xocs/dtd' xmlns:xs= 'http://www.w3.org/2001/XMLSchema' xmlns:xsi= 'http://www.w3.org/2001/XMLSchema-instance' xmlns= 'http://www.elsevier.com/xml/ja/dtd' xmlns:ja= 'http://www.elsevier.com/xml/ja/dtd' xmlns:mml= 'http://www.w3.org/1998/Math/MathML' xmlns:tb= 'http://www.elsevier.com/xml/common/table/dtd' xmlns:tbl_struct= 'http://www.elsevier.com/xml/table/dtd' \rangle$	0.6	6
22	Ultra-thin NbN films on Si: crystalline and superconducting properties. Journal of Physics: Conference Series, 2008, 97, 012045.	0.3	24
23	Temperature- and field-dependence of critical currents in NbN microbridges. Journal of Physics: Conference Series, 2008, 97, 012152.	0.3	10
24	Rare-earth intermetallic compounds at a magnetic instability. Journal of Alloys and Compounds, 2006, 408-412, 9-15.	2.8	6
25	Magnetotransport in. Physica B: Condensed Matter, 2006, 378-380, 44-45.	1.3	3
26	Hall effect across the quantum phase transition of CeCuAu. Physica B: Condensed Matter, 2005, 359-361, 86-88.	1.3	8
27	Study of 4H-SiC Schottky Diode Designs for 3.3kV Applications. Materials Science Forum, 0, 778-780, 795-799.	0.3	17
28	Two-Dimensional Carrier Profiling on Lightly Doped n-Type 4H-SiC Epitaxially Grown Layers. Materials Science Forum, 0, 821-823, 269-272.	0.3	2
29	Comparison of the Planar-JBS against the Trench-MOS Rectifier-Design Based on 4H-SiC for 3.3 kV Applications. Materials Science Forum, 0, 821-823, 604-607.	0.3	1
30	Optimization of 1700V 4H-SiC JBS Diode Parameters. Materials Science Forum, 0, 858, 782-785.	0.3	6
31	Junction Barrier Schottky (JBS) Rectifier Interface Engineering Facilitated by Two-Dimensional (2D) Dopant Imaging. Materials Science Forum, 0, 858, 497-500.	0.3	3
32	On the Influence of Active Area Design on the Performance of SiC JBS Diodes. Materials Science Forum, 0, 897, 471-474.	0.3	1